



ABSTRACT

-- ~~The present invention relates to a~~ A method of manufacturing a semiconductor device, ~~comprising~~ includes the steps of ~~[[;]]~~ forming a sunken section in an insulating film formed on a substrate ~~[[;]]~~ and forming a barrier metal film on ~~[[said]]~~ the insulating film inclusive of ~~[[said]]~~ the sunken section ~~[[;]]~~. The method also includes forming a copper-based film over the entire surface so as to fill up ~~[[said]]~~ the sunken section ~~[[;]]~~ and forming a copper-based metal interconnection, ~~which comprises the step of.~~ The interconnection is formed by polishing this substrate surface by the chemical mechanical polishing method, using a polishing slurry containing a silica polishing material, an oxidizing agent, an amino acid, a triazole-based compound and water, ~~wherein a.~~ A content ratio of ~~[[said]]~~ the amino acid to ~~[[said]]~~ the triazole-based compound (amino acid / triazole-based compound (weight ratio)) is 5 to 8.--